



DSS5240TQ

Description

This bipolar junction transistor (BJT) is designed to meet the stringent requirement of Automotive Applications.

Features

- BVCEO > -40V
- Ic = -2A High Continuous Collector Current
- ICM = -3A Peak Pulse Current
- Low Saturation Voltage -225mV Max @ Ic = -1A
- $R_{CE(sat)} = 90m\Omega$ at 0.5A for a Low Equivalent On-Resistance
- 730mW Power Dissipation
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DSS5240TQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/guality/product-definitions/

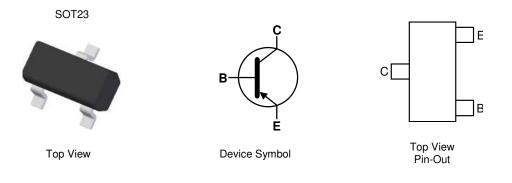
40V PNP LOW SATURATION TRANSISTOR IN SOT23

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (@)
- Weight 0.008 grams (Approximate)

Application

- Gate Driving MOSFETs and IGBTs
- Load Switch
- DC-DC Converters
- Battery Charging



Ordering Information (Note 4)

Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DSS5240TQ-7	Automotive	ZP2	7	8	3000

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

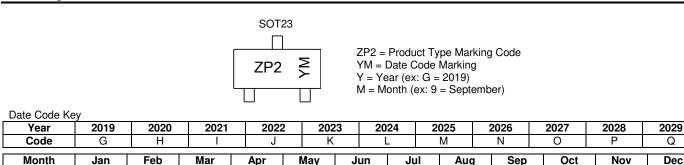
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and

Lead-free. 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

Notes:



5

1

3

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D



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	Vсво	-40	V
Collector-Emitter Voltage	VCEO	-40	V
Emitter-Base Voltage	VEBO	-5	V
Peak Pulse Collector Current	Ісм	-3	А
Continuous Collector Current	lc	-2	А
Base Current	lв	-300	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	PD	730	mW
Power Dissipation (Note 6)	PD	600	mW
Thermal Resistance, Junction to Ambient Air (Note 5)	Reja	171	°C/W
Thermal Resistance, Junction to Ambient Air (Note 6)	Reja	209	°C/W
Thermal Resistance, Junction to Lead (Note 7)	Rejl	75	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C

ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge—Human Body Model	ESD HBM	4000	V	3A
Electrostatic Discharge—Machine Model	ESD MM	400	V	С

Notes: 5. For a device mounted with the collector lead on 15mm × 15mm 1oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.

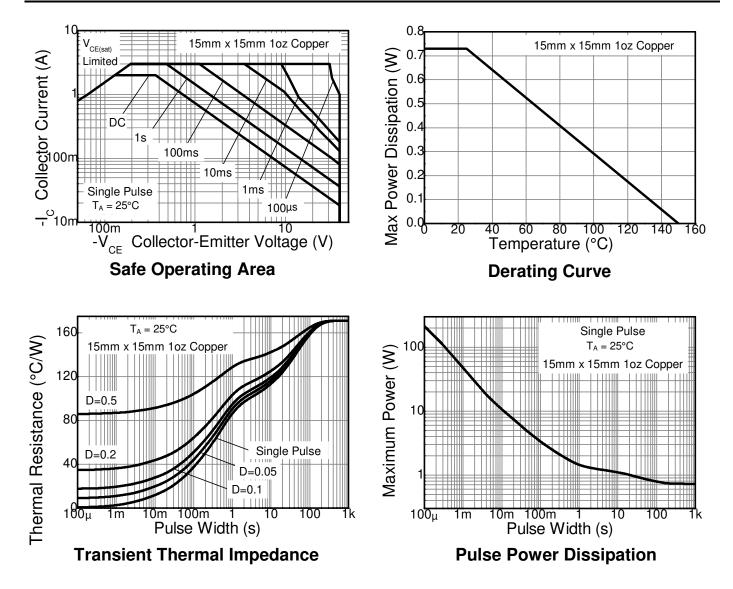
6. Same as Note 7, except the device is mounted on minimum recommended pad layout.

7. Thermal resistance from junction to solder-point (at the end of the collector lead).

8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information



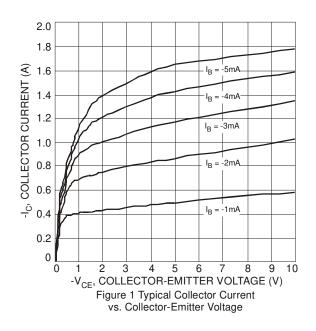


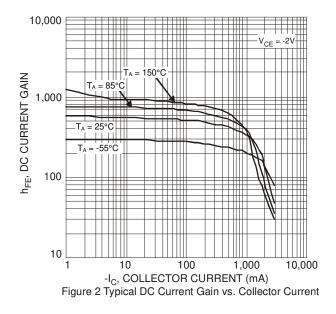
Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	ВУсво	-40	—	_	V	Ic = -100μA
Collector-Emitter Breakdown Voltage (Note 9)	BVCEO	-40	—	_	V	Ic = -10mA
Emitter-Base Breakdown Voltage	BVEBO	-5	—	_	V	$I_E = -100 \mu A$
Collector-Base Cutoff Current	Ісво		—	-100	nA	$V_{CB}=-30V,\ I_E=0$
	ICBO		—	-50	μA	$V_{CB} = -30V, \ I_E = 0, \ T_A = +150^{\circ}C$
Emitter-Base Cutoff Current	IEBO		—	-100	nA	$V_{EB} = -4V, I_{C} = 0$
ON CHARACTERISTICS (Note 9)						
		300	—	_		$V_{CE} = -2V, I_C = -0.1A$
DC Current Gain	b	260	—	_	_	$V_{CE} = -2V, I_C = -0.5A$
DC Current Gam	hfe	210	—	_		$V_{CE} = -2V$, $I_C = -1A$
		100	—	_		$V_{CE} = -2V$, $I_C = -2A$
			—	-100	mV	$I_{C} = -100 mA, I_{B} = -1 mA$
			-45	-110		$I_{C} = -500 \text{mA}, I_{B} = -50 \text{mA}$
Collector-Emitter Saturation Voltage	VCE(sat)		—	-225		$I_{C} = -750 \text{mA}, I_{B} = -15 \text{mA}$
			—	-225		Ic = -1A, I _B = -50mA
			—	-350		$I_{C} = -2A, I_{B} = -200mA$
Equivalent On-Resistance	RCE(sat)		90	220	mΩ	$I_{C} = -500 \text{mA}, I_{B} = -50 \text{mA}$
Base-Emitter Saturation Voltage	VBE(sat)		—	-1.1	V	Ic = -2A, I _B = -200mA
Base-Emitter Turn-on Voltage	V _{BE(on)}	_	_	-0.75	V	V _{CE} = -2V, I _C = -100mA
SMALL SIGNAL CHARACTERISTICS						
Transition Frequency	fт	100	_	—	MHz	$V_{CE} = -10V, I_C = -100mA, f = 100MHz$
Output Capacitance	Cobo	_	_	28	pF	V _{CB} = -10V, f = 1MHz

Note: 9. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%.

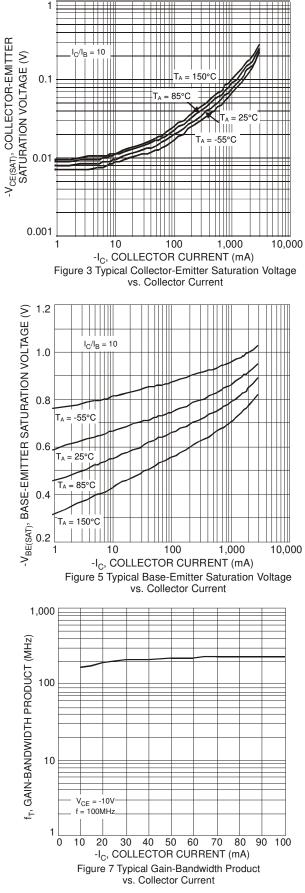
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)







Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.) (continued)



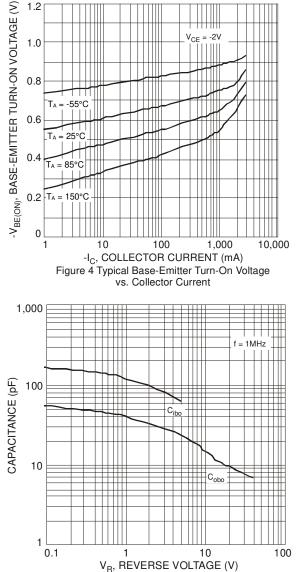
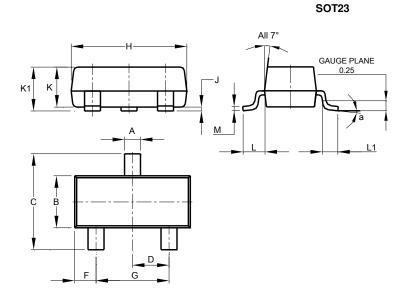


Figure 6 Typical Capacitance Characteristics



Package Outline Dimensions

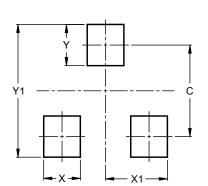
Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT23					
Dim	Min	Max	Тур		
Α	0.37	0.51	0.40		
В	1.20	1.40	1.30		
С	2.30	2.50	2.40		
D	0.89	1.03	0.915		
F	0.45	0.60	0.535		
G	1.78	2.05	1.83		
н	2.80	3.00	2.90		
J	0.013	0.10	0.05		
K	0.890	1.00	0.975		
K1	0.903	1.10	1.025		
L	0.45	0.61	0.55		
L1	0.25	0.55	0.40		
М	0.085	0.150	0.110		
а	0°	8°	_		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT23

Dimensions	Value (in mm)		
С	2.0		
Х	0.8		
X1	1.35		
Y	0.9		
Y1	2.9		



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